

Wai Yuen Fu

List of Publications by Year in descending order

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46
papers

985
citations

430754

18
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434063

31
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47
all docs

47
docs citations

47
times ranked

1238
citing authors

#	ARTICLE	IF	CITATIONS
1	Monolithic InGaN Multicolor Light-Emitting Devices. <i>Physica Status Solidi - Rapid Research Letters</i> , 2022, 16, .	1.2	5
2	Development of chipscale InGaN RGB displays using strain-relaxed nanosphere-defined nanopillars. <i>Nanotechnology</i> , 2022, 33, 285202.	1.3	2
3	Comparison of lasing characteristics of GaN microdisks with different structures. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 355107.	1.3	2
4	Phosphor-free InGaN nanopillar white LEDs by random clustering of mono-sized nanospheres. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	5
5	Whispering-gallery mode InGaN microdisks on GaN substrates. <i>Optics Express</i> , 2021, 29, 21280.	1.7	6
6	Electrically injected whispering-gallery mode InGaN/GaN microdisks. <i>Applied Physics Letters</i> , 2021, 119, 101106.	1.5	10
7	Strain-Induced Spectral Red-Shifting from Nanoscale Frustum Arrays Fabricated over InGaN/GaN Quantum Wells for Light-Emitting Applications. <i>ACS Applied Nano Materials</i> , 2021, 4, 666-672.	2.4	4
8	InGaN RGB Light-Emitting Diodes With Monolithically Integrated Photodetectors for Stabilizing Color Chromaticity. <i>IEEE Transactions on Industrial Electronics</i> , 2020, 67, 5154-5160.	5.2	29
9	Chip-scale GaN integration. <i>Progress in Quantum Electronics</i> , 2020, 70, 100247.	3.5	42
10	GaN microdisk with direct coupled waveguide for unidirectional whispering-gallery mode emission. <i>Optics Letters</i> , 2020, 45, 791.	1.7	16
11	Effect of Size on the Luminescent Efficiency of Perovskite Nanocrystals. <i>ACS Applied Energy Materials</i> , 2019, 2, 6998-7004.	2.5	7
12	Insight into the impact of atomic- and nano-scale indium distributions on the optical properties of InGaN/GaN quantum well structures grown on m-plane freestanding GaN substrates. <i>Journal of Applied Physics</i> , 2019, 125, 225704.	1.1	5
13	Intensity-Stabilized LEDs With Monolithically Integrated Photodetectors. <i>IEEE Transactions on Industrial Electronics</i> , 2019, 66, 7426-7432.	5.2	36
14	GaN monolithic integration for lighting and display. , 2019, , .		0
15	Designing microstructures for bandgap manipulation of InGaN Quantum Wells by k.p simulation coupled with molecular dynamics. , 2018, , .		0
16	Packaging of InGaN stripe-shaped light-emitting diodes. <i>Applied Optics</i> , 2018, 57, 2452.	0.9	4
17	Monolithically integrated InGaN/GaN light-emitting diodes, photodetectors, and waveguides on Si substrate. <i>Optica</i> , 2018, 5, 564.	4.8	102
18	Explaining relative spectral red shifts in InGaN/GaN micropillars. <i>Optica</i> , 2018, 5, 765.	4.8	9

#	ARTICLE	IF	CITATIONS
37	Structural Characterisation of Improved GaN Epilayers Grown on a Ge(111) Substrate. Applied Physics Express, 2011, 4, 091001.	1.1	3
38	Nanosphere Lithography for Nitride Semiconductors. , 2010, , .		1
39	Room temperature photonic crystal band-edge lasing from nanopillar array on GaN patterned by nanosphere lithography. Journal of Applied Physics, 2010, 107, 063104.	1.1	12
40	Close-packed hemiellipsoid arrays: A photonic band gap structure patterned by nanosphere lithography. Applied Physics Letters, 2009, 95, 133125.	1.5	33
41	A novel GaN photonic crystal structure comprising nanopillars with inclined sidewalls. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S639-S642.	0.8	1
42	Metallic nanoparticle array on GaN by microsphere lithography. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S654-S657.	0.8	11
43	Evaluation of InGaN/GaN light-emitting diodes of circular geometry. Optics Express, 2009, 17, 22311.	1.7	31
44	Geometrical Shaping of InGaN Light-Emitting Diodes by Laser Micromachining. IEEE Photonics Technology Letters, 2009, 21, 1078-1080.	1.3	41
45	Polychromatic light-emitting diodes with a fluorescent nanosphere opal coating. Nanotechnology, 2008, 19, 355203.	1.3	32
46	GaN PNP Light-Emitting Bipolar Junction Transistor. Journal Physics D: Applied Physics, 0, , .	1.3	7